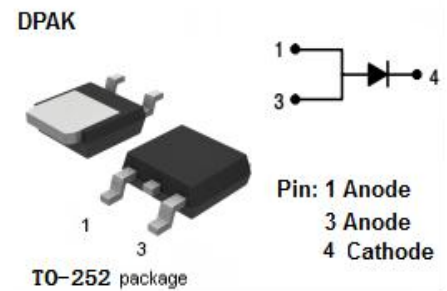


## Schottky Barrier Rectifier

### FEATURES

- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### APPLICATIONS

- For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, DC-to-DC converters or polarity protection application.

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>RRM</sub> V <sub>RMS</sub> V <sub>R</sub>	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	35	V
I <sub>F(AV)</sub>	Average Rectified Forward Current	8	A
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	175	A
T <sub>J</sub>	Junction Temperature	-65~125	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.8	°C/W

**ELECTRICAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	TYP	MAX	UNIT
$V_F$	Maximum Instantaneous Forward Voltage	$I_F = 8\text{ A}; T_j = 25^\circ\text{C}$		0.51	V
		$I_F = 8\text{ A}; T_j = 125^\circ\text{C}$		0.41	
$I_R$	Maximum Instantaneous Reverse Current	$V_R = V_{RRM}; T_j = 25^\circ\text{C}$		1.4	mA
		$V_R = V_{RRM}; T_j = 100^\circ\text{C}$		35	

**Package Dimensions**

